

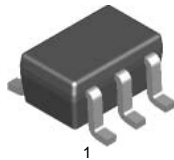
2N7002DW

N-Channel Enhancement Mode Field Effect Transistor

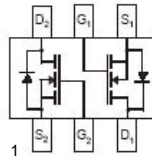
Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant

SC70-6 (SOT363)



Marking : 2N



Absolute Maximum Ratings * $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{DGR}	Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	60	V
V_{GSS}	Gate-Source Voltage	Continuous	± 20
		Pulsed	± 40
I_D	Drain Current	Continuous	115
		Continuous @ 100°C	73
		Pulsed	800
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Total Device Dissipation Derating above $T_A = 25^\circ\text{C}$	200	mW
		1.6	$\text{mW}/^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	625	$^\circ\text{C}/\text{W}$

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, Minimum land pad size,

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	MIN	TYP	MAX	Units
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Off Characteristics (Note1)

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	60	78	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 60V, V_{GS} = 0V, @T_C = 125^\circ\text{C}$	-	0.001 7	1.0 500	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	0.2	± 10	nA

On Characteristics (Note1)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.76	2.0	V
$R_{DS(ON)}$	Satic Drain-Source On-Resistance	$V_{GS} = 5V, I_D = 0.05A,$ $V_{GS} = 10V, I_D = 0.5A, @T_j = 125^\circ\text{C}$	- -	1.6 2.53	7.5 13.5	Ω
$I_{D(ON)}$	On-State Drain Current	$V_{GS} = 10V, V_{DS} = 7.5V$	0.5	1.43	-	A
g_{FS}	Forward Transconductance	$V_{DS} = 10V, I_D = 0.2A$	80	356.5	-	mS

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	37.8	50	pF
C_{oss}	Output Capacitance		-	12.4	25	pF
C_{rss}	Reverse Transfer Capacitance		-	6.5	7.0	pF

Switching Characteristics

$t_{D(ON)}$	Turn-On Delay Time	$V_{DD} = 30V, I_D = 0.2A, V_{GEN} = 10V$ $R_L = 150\Omega, R_{GEN} = 25\Omega$	-	5.85	20	ns
$t_{D(OFF)}$	Turn-Off Delay Time		-	12.5	20	

Note1 : Short duration test pulse used to minimize self-heating effect.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

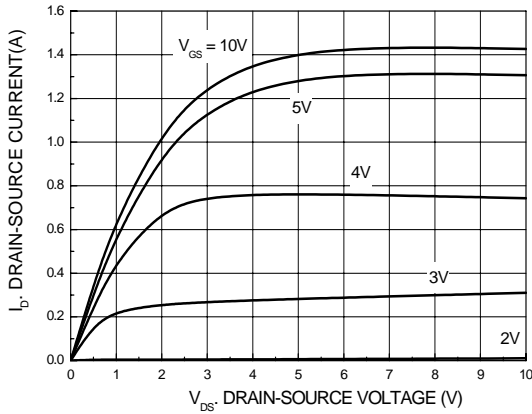


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

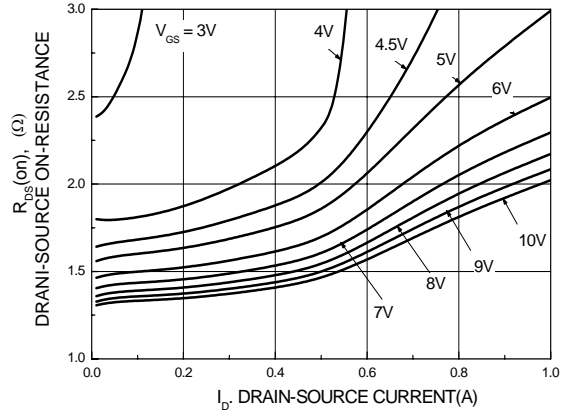


Figure 3. On-Resistance Variation with Temperature

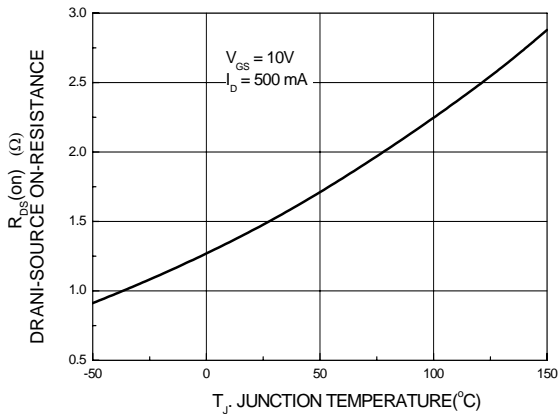


Figure 4. On-Resistance Variation with Gate-Source Voltage

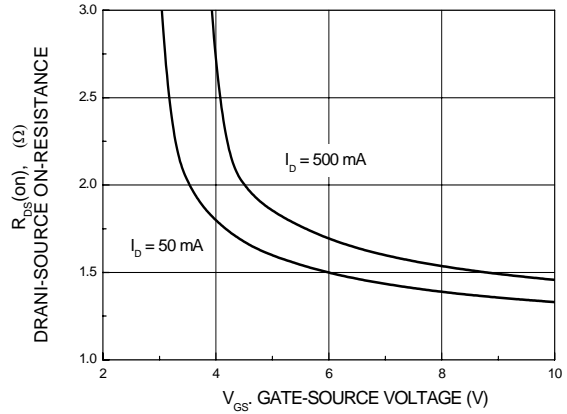


Figure 5. Transfer Characteristics

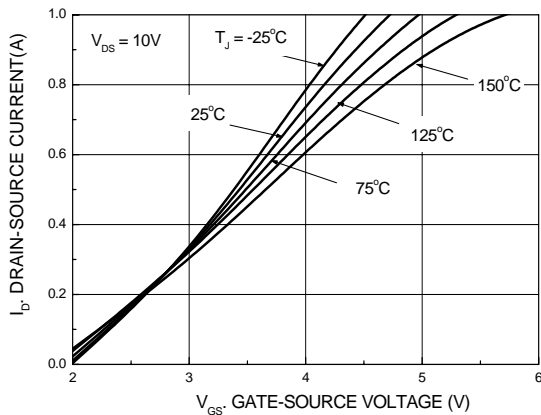
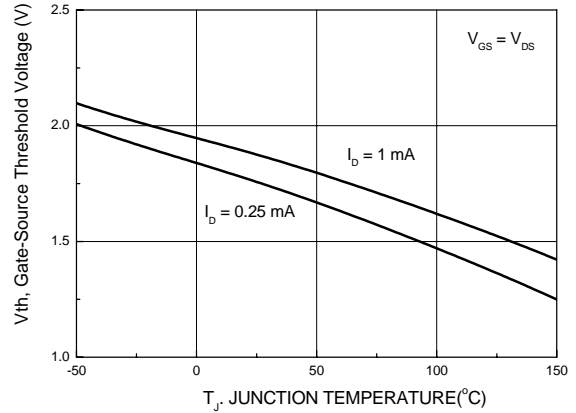


Figure 6. Gate Threshold Variation with Temperature



Typical Performance Characteristics

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

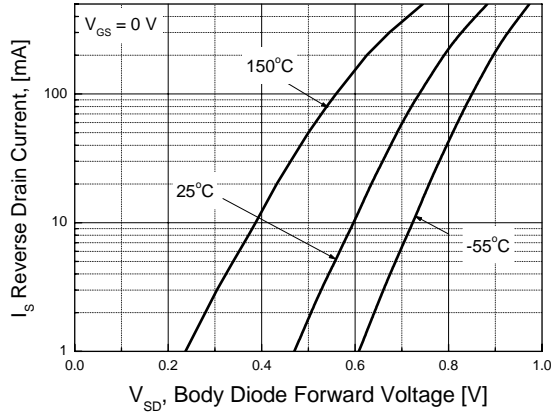
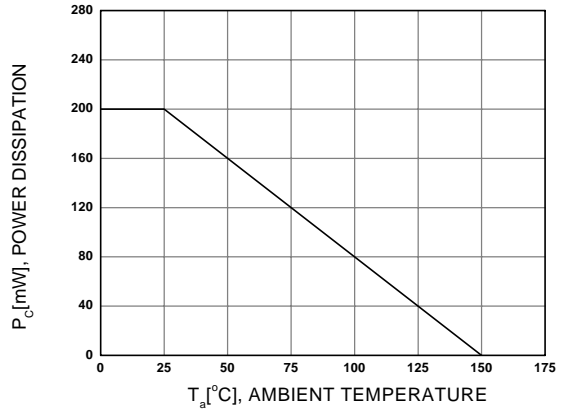
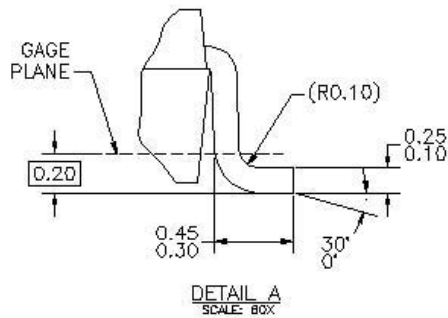
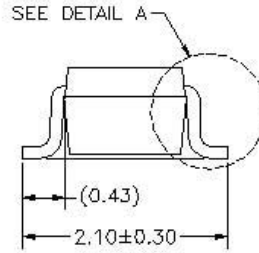
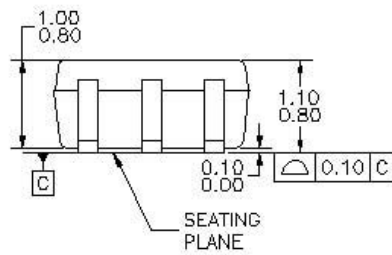
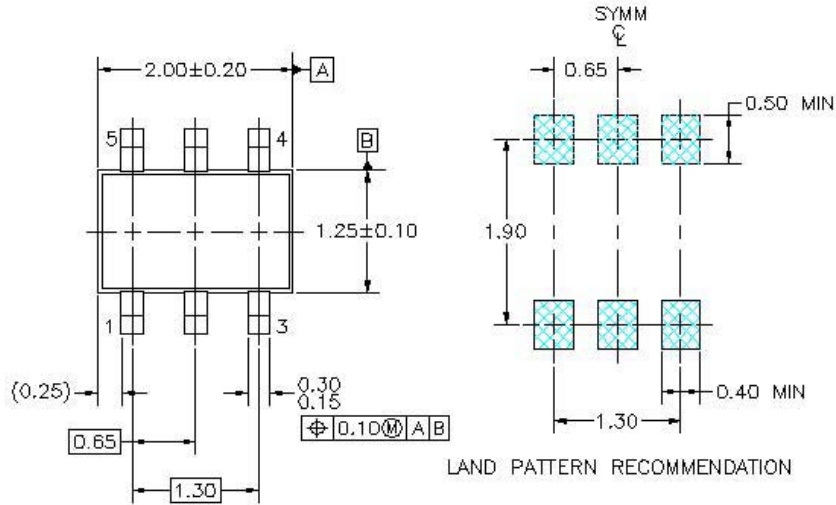


Figure 8. Power Derating



Package Dimensions

SC70-6 (SOT-363)




NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-66, 1996.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH.



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